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Vishay Siliconix

DG2522

Low Voltage, Fault Protection, SP3T Analog Switch (3:1 Multiplexer/Demultiplexer)

DESCRIPTION

ISHA

The DG2522 is a low on-resistance SP3T analog switch design to operation from 1.6 V to 5.5 V.

The DG2522 switches signals in either direction with amplitudes up to V+. Protection circuit is built in to isolate the signals if any of them swings above V+. It guaranteed low leakage level for isolation in power down mode.

Built on Vishay Siliconix's sub-micro CMOS technology, the DG2522 achieves switch on-resistance of 0.8 Ω at 4.5 V V+ with 0.6 Ω flatness. It has superior 0.008 % THD (total harmonic distortion) over frequency of 20 Hz to 20 kHz. It provides - 59 dB off-Isolation, - 65 dB crosstalk at 1 MHz, and 105 MHz - 3 dB bandwidth.

The select pin of the control logic input can tolerate voltages above V+ up to 5.5 V. Logic high 1.8 V is guaranteed over the full V+ range that makes it compatible with many low voltage digital control circuits.

The features of ultra small package size, wide V+ range, low on-resistance, low logic threshold, and switch isolation under fault condition make it an ideal device for battery operated devices to handle signals such as audio, video, data stream, and other high accuracy signals.

The DG2522 comes in a small miniQFN-8 lead package of 1.4 mm x 1.4 mm x 0.55 mm. As a committed partner to the community and the environment, Vishay Siliconix manufactures this product with the lead (Pb)-free device termination and is 100 % RoHS compliant.

FEATURES

- Isolation at V+ = 0 V and signal above V+
- Logic input tolerates up to 5.5 V
- 1.6 V to 5.5 V operation voltage range
- Guaranteed 1.8 V V_{TH(high)} at V+ = 4.5 V
- 0.008 % total harmonic distortion
- Low switch on-resistance
- 300 mA latch up current per JESD78

BENEFITS

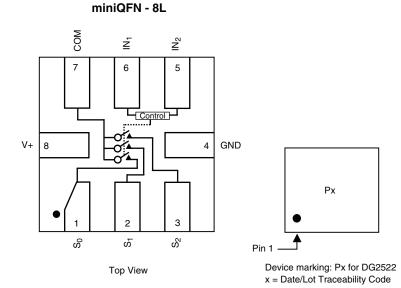
- Ultra small miniQFN8 package of 1.4 mm x 1.4 mm x 0.55 mm
- High fidelity audio switch
- Reed relay replacement
- Low power consumption

APPLICATIONS

- Cellular phones and PDAs ٠
- GPS and portable media players
- Modems and wireless cards
- Computers peripherals
- Communication and network circuits
- Low voltage data acquisition systems
- Portable instrumentation

FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION

DG2522









TRUTH TABLE DG2522					
IN ₁ (Pin 6)	IN ₂ (Pin 5)	Function			
0	0	COM diconnect			
1	0	COM (Pin 7) = S_0 (Pin 1)			
0	1	COM (Pin 7) = S_1 (Pin 2)			
1	1	COM (Pin 7) = S_2 (Pin 3)			

ORDERING INFORMATION					
Temp. Range	Package	Part Number			
- 40 °C to 85 °C	miniQFN-8L	DG2522DN-T1-E4			

ABSOLUTE MAXIMUM RATINGS $T_A = 25 \degree C$, unless otherwise noted				
Parameter		Limit	Unit	
Deference to CND	V+	- 0.3 to 6.0	V	
Reference to GND	IN, COM, S _X ^a	- 0.3 to (V+ + 0.3)	V	
Current (Any terminal except S _X or COM	Λ)	30		
Continuous Current (S _X or COM)		± 300	mA	
Peak Current (Pulsed at 1 ms, 10 % duty cycle)		± 500	7	
Storage Temperature (D Suffix)		- 65 to 150	°C	
Power Dissipation (Packages) ^b	miniQFN-8L ^c	190	mW	

Notes:

a. Signals on S0, S1, S2 and COM or IN exceeding V+ will be clamped by internal diodes. Limit forward diode current to maximum current ratings.

b. All leads welded or soldered to PC board.

c. Derate 2.4 mW/°C above 70 °C.



		Test Conditions Unless Otherwise Specified		Limits - 40 °C to 85 °C			
Parameter	Symbol	$V + = 5 V, \pm 10 \%, V_{IN} = 0.6 V \text{ or } 1.8 V^{e}$	Temp. ^a	Min. ^b	Typ. ^c	Max. ^b	Unit
Analog Switch	•				•		
Analog Signal Range ^d	V _{analog}	R _{DS(on)}	Full	0		V+	V
On-Resistance		V+ = 4.5 V, I_{SX} = 100 mA, V_{COM} = 2.5 V	Room		0.8	1.1	
On-nesistance	R _{DS(on)}	V+ = 4.5 V, I_{SX} = 100 mA, V_{COM} = 2.5 V	Full			1.5	
R _{ON} Match	ΔR_{ON}	V+ = 4.5 V, I_{SX} = 100 mA, V_{COM} = 2.5 V	Room			0.1	Ω
R _{ON} Resistance Flatness	R _{ON} flatness	V+ = 4.5 V, I _{SX} = 100 mA, V _{COM} = 0.5 V, 2.5 V	Room		0.2	0.6	
	1		Room	- 20		20	
Switch Off Leakage	I _{SX(off)}	V+ = 5.5 V, V _{SX} = 1 V/4.5 V,	Full	- 120		120	
Current	1	$V_{COM} = 4.5 V/1 V$	Room	- 20		20	
	I _{COM(off)}		Full	- 120		120	nA
Channel-On Leakage	1	V+ = 4.3 V, V _{SX} = V _{COM} = 4.5 V/1 V	Room	- 20		20	
Current	I _{COM(on)}	$v + = 4.3 v, v_{SX} = v_{COM} = 4.3 v/1 v$	Full	- 120		120	
Power Down Leakage			Room	- 1	0.001	1	μA
Power Down Leakage		$V + = 0 V, V_{SX} = 0 V/5.5 V, V_{COM} = 5.5 V/0 V$	Full	- 25		25	
Digital Control							
Input High Voltago	V _{INH}	V+ = 2.7 V	Full	1.6			v
Input High Voltage		V+ = 4.5 V	Full	1.8			
Input Low Voltage	V _{INL}	V+ = 4.5 V	Full			0.6	
Input Capacitance	C _{IN}	$f = 1 MHz, V_{INx} = 0 V$	Room		5		pF
Input Current	$I_{\rm INL}$ or $I_{\rm INH}$	$V_{IN} = 0 \text{ or } V+$	Full	- 1		1	μA
Dynamic Characteristics							
Break-Before-Make Time ^e	t _{BBM}	$V+ = 5.0 V, V_{SX} = V+,$	Room		8		ns
Break Belore Make Time		$R_L = 50 \Omega$, $C_L = 35 pF$ (see figure 2)	Full	14			
Enable Turn-On Time ^e	t _{ON}		Room		53	75	
		$V+ = 5.0 V, V_{SX} = V+,$	Full			85	
Enable Turn-Off Time ^e		$R_L = 50 \Omega$, $C_L = 35 pF$ (see figure 1)	Room		40	60	
	*0FF		Full			70	
Charge Injection ^d	Q	C_L = 1 nF, R_{GEN} = 0 Ω , V_{GEN} = 0 V	Room		27		рС
Off-Isolation ^d	O _{IRR}	R_L = 50 Ω, C_L = 5 pF, f = 1 MHz	Room —		- 59		dB
Crosstalk ^d	X _{TALK}	R_L = 50 Ω, C_L = 5 pF, f = 1 MHz	noom		- 64		uD
- 3 dB Bandwidth ^d	BW	$R_L = 50 $ Ω, $C_L = 5 $ pF	Room		105		MHz
Source Off Capacitance ^d	C _{SX(off)}	$f = 1 MHz, V_{NX} = 0 V$	Room		17		
Drain Off Capacitance ^d	C _{COM(off)}	$f = 1 MHz, V_{COM} = 0 V$	Room		51		pF
Drain On Capacitance ^d	C _{COM(on)}	$f = 1 MHz$, $V_{COM} = V_{NX} = 0 V$	Room		70		
		V+ = 5 V, V _{IN} = 1 V _{RMS} , R _L = 600 Ω f = 20 Hz to 20 kHz	Room		0.008		%
Power Supply						•	
Power Supply Range	V+			1.6		5.5	V
Power Supply Current	l+	V _{IN} = 0 or V+	Full			1.0	μA

Notes:

a. Room = 25 °C, Full = as determined by the operating suffix.

b. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.

c. Typical values are for design aid only, not guaranteed nor subject to production testing.

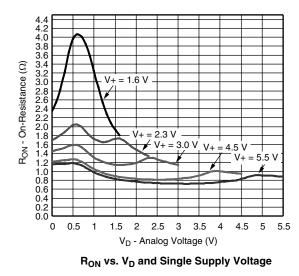
d. Guarantee by design, not subjected to production test.

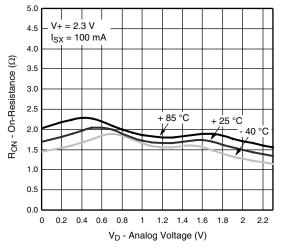
e. V_{IN} = input voltage to perform proper function.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

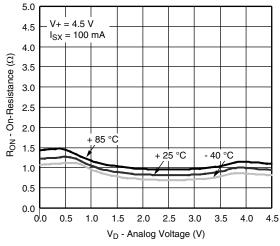
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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

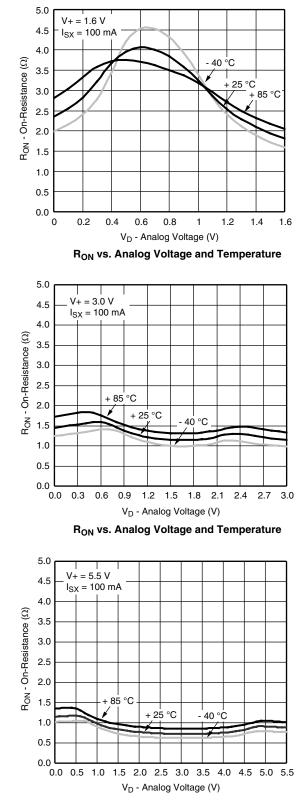




R_{ON} vs. Analog Voltage and Temperature



R_{ON} vs. Analog Voltage and Temperature

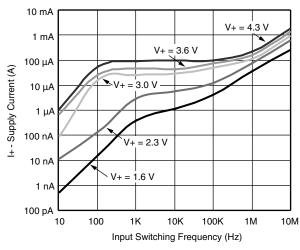


R_{ON} vs. Analog Voltage and Temperature

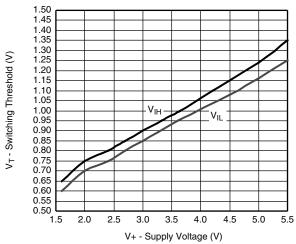


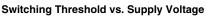
DG2522 Vishay Siliconix

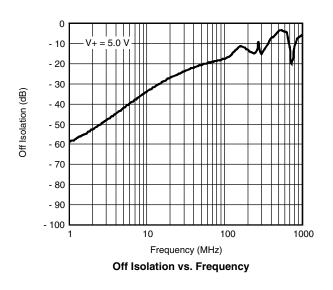
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

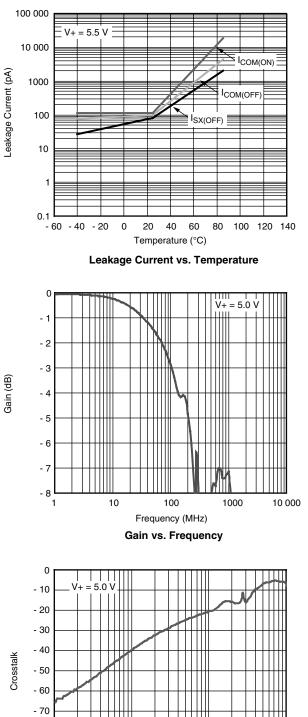










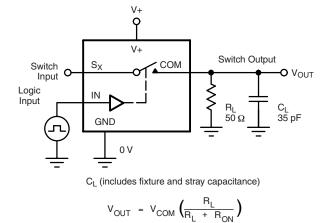


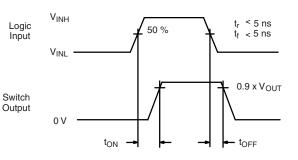
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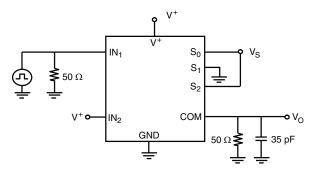
TEST CIRCUITS

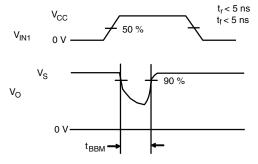




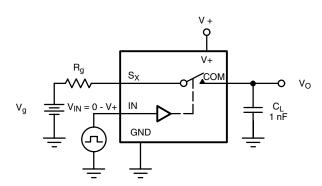
Logic "1" = Switch On Logic input waveforms inverted for switches that have the opposite logic sense.











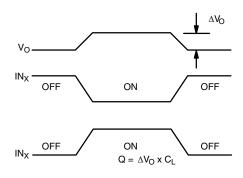


Figure 3. Charge Injection



TEST CIRCUITS

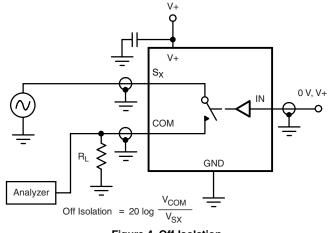
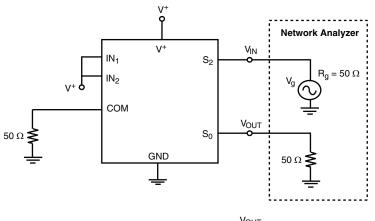


Figure 4. Off-Isolation



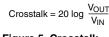


Figure 5. Crosstalk

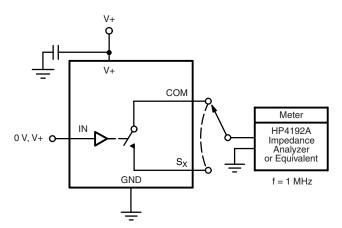


Figure 6. Channel Off/On Capacitance

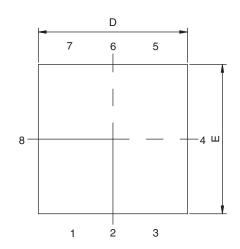
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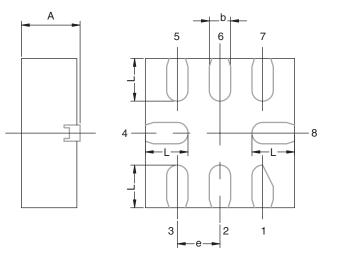


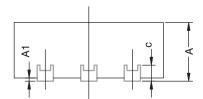
Package Information

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MINIQFN-8L CASE OUTLINE



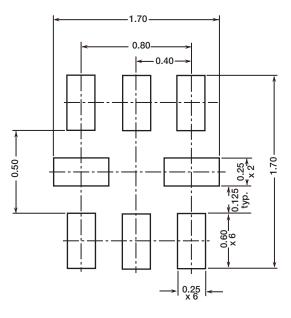




	MILLIMETERS			INCHES		
DIM	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
А	0.50	0.55	0.60	0.0197	0.0217	0.0236
A1	0.00	-	0.05	0.000	-	0.002
b	0.15	0.20	0.25	0.006	0.008	0.010
С	0.15 REF			0.006 REF		
D	1.35	1.40	1.45	0.053	0.055	0.057
E	1.35	1.40	1.45	0.053	0.055	0.057
е	0.40 BSC			0.016 BSC		
L	0.35	0.40	0.45	0.014	0.016	0.018
ECN: C-08336-Re DWG: 5964	ev. A, 05-May-08				·	



RECOMMENDED MINIMUM PADS FOR MINI QFN 8L



Suggested Minimum Pad Dimensions in mm



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